

**Amendments to the Specification:**

Please replace the paragraph bridging pages 12 and 13 with the following amended paragraph:

FIG. 4A shows a structure in which, over an adhesive 41 on a first label 40, a metal oxide 42, an oxide film 43 containing silicon, a base film 44 including an insulating film containing nitrogen, a semiconductor film 45 having an impurity region, a gate electrode 64 over a gate insulating film 65, a first interlayer insulating film 46 covering a gate electrode 64, a second interlayer insulating film 47, a wiring 63 connected to an impurity region, an antenna ~~[[49]]~~ 31 in the same layer as the wiring 63, protective film 49 covering the wiring and the antenna, and the second label 50 over the protective film are provided. Note that the similar structure without the antenna may be used for a contact thin film integrated circuit.

Please replace the paragraph bridging pages 13 and 14 with the following amended paragraph:

FIG. 4B shows an example of forming an antenna ~~[[51]]~~ 31 in the same layer as a gate electrode, unlike in the case of FIG. 4A. The antenna is formed by etching a predetermined pattern using a gate material concurrently with the formation of wiring, formed by ink-jet or a printing method using a conductive paste (specifically, silver paste), or pouring an antenna material into a depressed portion that is formed in the first interlayer insulating film or in the gate insulating film. Note that the similar structure without the antenna may be used for a contact thin film integrated circuit.

Please replace the paragraph beginning at page 14, line 5, with the following amended paragraph:

FIG. 4C shows another example of forming the antenna and the IC area separately, unlike in FIGs. 4A and 4B. The IC having the CPU and the memory are transferred to a predetermined position, and an antenna 31 is formed by ink-jet or by a printing method using a conductive paste (specifically, silver paste). The conductive paste is covered over by a protective film 49. A protective film different from the protective film 49 may be used alternatively. At that point, the antenna and the integrated circuit area may be disposed appropriately. Note that the similar structure without the antenna may be used for a contact thin film integrated circuit.